



## 30V P-Channel Enhancement Mode MOSFET - ESD Protected

Voltage

-30 V

Current

-1.1A

#### **Features**

- RDS(ON), VGS@-4,5V, ID@-1.1A<370mΩ</li>
- RDS(ON), VGS@-2.5V, ID@-0.5A<540mΩ</li>
- RDS(ON) , VGS@-1.8V, ID@-0.1A<970mΩ</li>
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

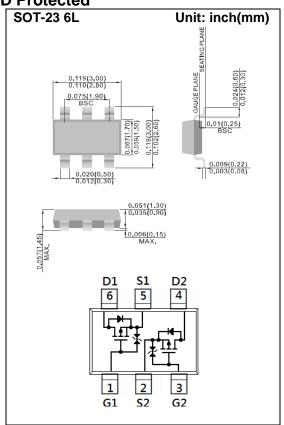
## **Mechanical Data**

• Case: SOT-23 6L Package

Terminals : Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0005 ounces, 0.0141 grams

Marking: SG3



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER  |                      | SYMBOL          | LIMIT      | UNITS |
|--|----------------------|-----------------|------------|-------|
| Drain-Source Voltage                             |                      | V <sub>DS</sub> | -30        | V     |
| Gate-Source Voltage                              |                      | $V_{GS}$        | <u>+</u> 8 | V     |
| Continuous Drain Current                         |                      | I <sub>D</sub>  | -1.1       | Α     |
| Pulsed Drain Current (Note 4)                    |                      | I <sub>DM</sub> | -4.4       | Α     |
| Power Dissipation                                | T <sub>a</sub> =25°C | P <sub>D</sub>  | 1.25       | W     |
|  | Derate above 25°C    |                 | 10         | mW/°C |
| Operating Junction and Storage Temperature Range |                      | $T_J, T_{STG}$  | -55~150    | °C    |
| Typical Thermal resistance                       |                      |                 |            |       |
| - Junction to Ambient (Note 3)                   |                      | $R_{\theta JA}$ | 100        | °C/W  |





# Electrical Characteristics (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION  | MIN. | TYP.         | MAX.        | UNITS |
|----------------------------------|---------------------|---|------|--------------|-------------|-------|
| Static                           |                     |   |      |              |             |       |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA   | -30  | -            | -           | V     |
| Gate Threshold Voltage           | $V_{GS(th)}$        | $V_{DS}=V_{GS}$ , $I_{D}=-250uA$  | -0.5 | -0.98        | -1.3        | V     |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.1A   | -    | 293          | 370         | mΩ    |
|                                  |                     | V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-0.5A   | -    | 387          | 540         |       |
|                                  |                     | V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-0.1A   | -    | 750          | 970         |       |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V  | -    | -0.01        | -1          | uA    |
| Gate-Source Leakage Current      | $I_{GSS}$           | $V_{GS}=\underline{+}8V, V_{DS}=0V$   | -    | <u>+</u> 3.4 | <u>+</u> 10 | uA    |
| Dynamic <sup>(Note 5)</sup>      |                     |   |      |              |             |       |
| Total Gate Charge                | $Q_g$               | V <sub>DS</sub> =-15V, I <sub>D</sub> =-1.1A,<br>V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup> | -    | 1.6          | -           | nC    |
| Gate-Source Charge               | $Q_gs$              |   | -    | 0.5          | -           |       |
| Gate-Drain Charge                | $Q_gd$              |   | -    | 0.3          | -           |       |
| Input Capacitance                | Ciss                | V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V,<br>f=1.0MHZ                                       | -    | 125          | -           | pF    |
| Output Capacitance               | Coss                |   | -    | 22           | -           |       |
| Reverse Transfer Capacitance     | Crss                |   | -    | 6            | -           |       |
| Turn-On Delay Time               | td <sub>(on)</sub>  | $V_{DD}$ =-15V, $I_{D}$ =-1.1A, $V_{GS}$ =-4.5V, $R_{G}$ =6 $\Omega$ (Note 1,2)               | -    | 11           | -           | ns    |
| Turn-On Rise Time                | tr                  |   | -    | 51           | -           |       |
| Turn-Off Delay Time              | td <sub>(off)</sub> |   | -    | 65           | -           |       |
| Turn-Off Fall Time               | tf                  | K <sub>G</sub> =012   | -    | 46           | -           |       |
| Drain-Source Diode               |                     |   |      |              |             |       |
| Maximum Continuous Drain-Source  |                     |   |      |              | 4.0         | А     |
| Diode Forward Current            | I <sub>S</sub>      |   | -    | -            | -1.0        |       |
| Diode Forward Voltage            | $V_{SD}$            | I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V  | -    | -0.9         | -1.2        | V     |

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

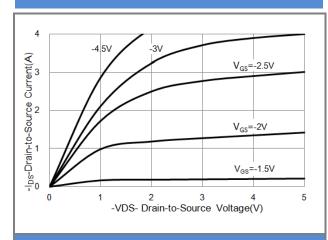
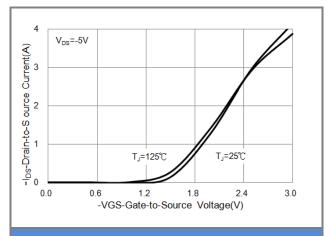


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

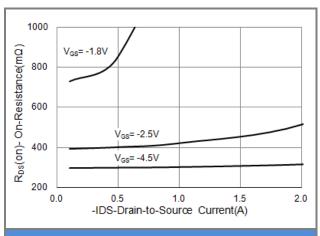


Fig.3 On-Resistance vs. Drain Current

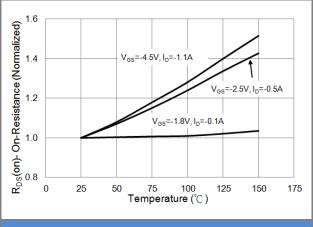


Fig.4 On-Resistance vs. Junction temperature

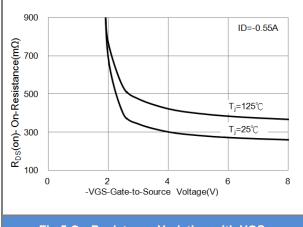
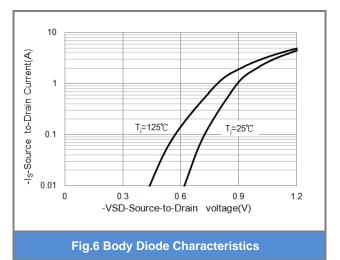


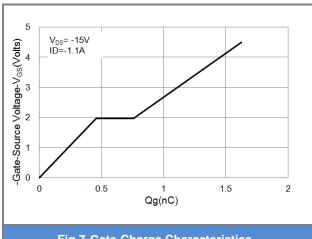
Fig.5 On-Resistance Variation with VGS.







## **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

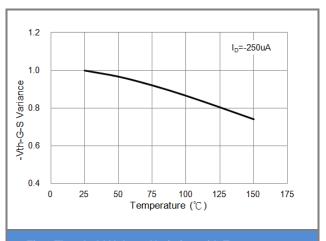


Fig.8 Threshold Voltage Variation with Temperature.

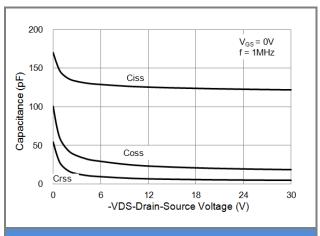


Fig.9 Capacitance vs. Drain-Source Voltage.

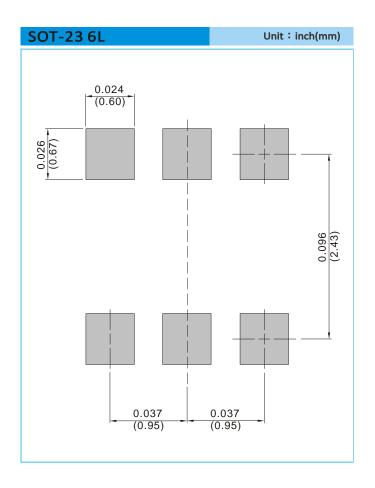




## PART NO PACKING CODE VERSION

| PART NO PACKING CODE | Package Type | Packing type       | Marking | Version      |
|----------------------|--------------|--------------------|---------|--------------|
| PJS6833_S1_00001     | SOT-23 6L    | 3K pcs / 7" reel   | SG3     | Halogen free |
| PJS6833_S2_00001     | SOT-23 6L    | 10K pcs / 13" reel | SG3     | Halogen free |

## **MOUNTING PAD LAYOUT**







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